

CONCEPT MAP

Electronic Devices

Band Theory:

- In metal, the conduction band and valence band partially overlap each other.
- In semiconductors, valence band is completely filled and conduction band is empty.

Forbidden Band:
The energy gap between the valence band and conduction band.
$$E_g = h\nu = \frac{hc}{\lambda}$$

Valence Band:
It may be partially or completely filled with electrons.

Conduction Band:
It is either empty or partially filled.

Energy Bands in Solids

Semiconductor:
Solids which have low conductivity and high resistivity.

Electrical Conductivity: The conductivity of the semiconductor is given by
$$\sigma = e(n_e\mu_e + n_h\mu_h)$$

Logic Gates: A digital circuit with one or more input signals but only one output signal is known as logic gate.

Extrinsic Semiconductor:
It is a doped semiconductor.

Intrinsic Semiconductor:
It is free from every impurity. eg. Ge and Si

OR Gate: Output is high if any or all the inputs are high.
$$Y = A + B$$

AND Gate: Output is high only when all the inputs are high. $Y = A \cdot B$

Zener Diode: It is designed to operate under reverse bias in the breakdown region and is used as a voltage regulator.

n-type Semiconductor:
Conduction of electricity is due to motion of electrons.

p-type Semiconductor:
Conduction of electricity is due to motion of holes.

NOT Gate: It inverts the input, so it is also called inverter.
$$Y = \bar{A}$$

NAND Gate: It is an AND gate followed by NOT gate
$$Y = \overline{A \cdot B}$$

Transistor: A transistor is basically a silicon or germanium crystal containing three separate regions. It can either be n-p-n type or p-n-p type.

p-n Junction Diode: When donor impurities are introduced into one side and acceptors into the other side of a single crystal of an intrinsic semiconductor, a p-n junction is formed.

XOR Gate: The Boolean expression for XOR gate is
$$Y = \bar{A}B + A\bar{B}$$

$$= A \oplus B$$

NOR Gate: It is an OR gate followed by NOT gate.
$$Y = \overline{A + B}$$

Transistor as an Amplifier:
When the transistor is used in the active region, it acts as an amplifier.

Transistor as a Switch: When the transistor is used in the cut off region or saturation region, it acts as a switch.

Transistor as an Oscillator:
The frequency of the oscillation is given by
$$\nu = \frac{1}{2\pi\sqrt{LC}}$$

Half Wave Rectifier:

- Peak value of current is
$$I_m = \frac{V_m}{r_f + R_L}$$
- rms value of current is
$$I_{rms} = \frac{I_m}{2}$$
- dc value of current is
$$I_{dc} = \frac{I_m}{\pi}$$
- Peak inverse voltage is
P.I. $V = V_m$
- dc value of voltage is
$$V_{dc} = I_{dc}R_L = \frac{I_m}{\pi}R_L$$

Full Wave Rectifier:

- Peak value of current is
$$I_m = \frac{V_m}{r_f + R_L}$$
- rms value of current is
$$I_{rms} = \frac{I_m}{\sqrt{2}}$$
- dc value of current is
$$I_{dc} = \frac{2I_m}{\pi}$$
- Peak inverse voltage is
P.I. $V = 2V_m$
- dc value of voltage is
$$V_{dc} = I_{dc}R_L = \frac{2I_m}{\pi}R_L$$

XNOR Gate: The Boolean expression for XNOR gate is
$$Y = AB + \bar{A}\bar{B}$$

$$= \bar{A} \oplus B$$

Symbol Used

h = Planck's constant	L = inductance
ν = frequency	C = capacitance
c = velocity of light	n_e = electron density
λ = wavelength of radiation	n_h = hole density
μ_h = holes mobility	
μ_e = electron mobility	